

CYPD1104-35FNXIT Datasheet

# USB Type-C Port Controller with Power Delivery

### **General Description**

CCG1 provides a complete USB Type-C and USB Power Delivery port control solution. The core architecture of CCG1 enables a base Type-C solution that can scale to a complete 100-W USB Power Delivery with Alternate Mode multiplex support. CCG1 is also a Type-C cable ID IC for active and passive cables. The CCG1 controller detects connector insert, plug orientation and VCONN switching signals. CCG1 makes it easier to add USB Power Delivery to any architecture because it provides control signals to manage external VBUS and V<sub>CONN</sub> power management solutions and external mux controls for most single cable-docking solutions.

The CCG1 family of devices are fixed-function parts that use a configuration table to control their operation in different applications. The functionality is implemented in firmware and will be certified against USB Implementers Forum (USB-IF) compliance tests when available. The programmability allows CCG1 devices to track any USB Specification changes. For information on accessing the source code, contact Cypress support.

### Applications

USB Type-C active cables

### Features

### 32-bit MCU Subsystem

■ 48-MHz ARM Cortex-M0 CPU with 32-KB flash and 4-KB SRAM

### Integrated analog blocks

- 12-bit, 1-Msps ADC for VBUS voltage and current monitoring
- Dynamic overcurrent and overvoltage protection

### Integrated digital blocks

- Two configurable 16-bit TCPWM blocks
- One I<sup>2</sup>C master or slave

### Figure 1. CCG1 Block Diagram<sup>[2, 3, 4, 5, 6, 7]</sup>

### Type-C Support

- Integrated transceiver (BB PHY)
- Supports up to two USB ports with PD
- Supports routing of all protocols through an external mux

### PD Support

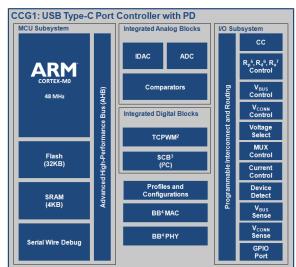
- Supports Provider and Consumer roles
- Supports all power profiles

### Low-Power Operation

- 1.8-V to 5.5-V operation
- Sleep 1.3 mA, Deep Sleep 1.3 µA<sup>[1]</sup>

### Packages

35-ball wafer-level CSP (WLCSP)



#### Notes

Values measured for CCG1 silicon only. Application specific power numbers may be higher. 1

•

- Timer, counter, pulse-width modulation block 2
- Serial communication block configurable as I<sup>2</sup>C. 3. 4
- Base band
- Termination resistor denoting a Downstream Facing Port (DFP). 5 6
- Termination resistor denoting a Upstream Facing Port (UFP). Termination resistor denoting an Electronically Marked Cable Assembly (EMCA). 7

Cypress Semiconductor Corporation Document Number: 001-97904 Rev. \*\*

198 Champion Court

San Jose, CA 95134-1709



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### **Functional Definition**

#### **CPU and Memory Subsystem**

#### CPU

The Cortex-M0 CPU in the CCG1 is part of the 32-bit MCU subsystem, which is optimized for low-power operation with extensive clock gating. It mostly uses 16-bit instructions and executes a subset of the Thumb-2 instruction set. This enables fully compatible binary upward migration of the code to higher performance processors such as the Cortex-M3 and M4, thus enabling upward compatibility. The Cypress implementation includes a hardware multiplier that provides a 32-bit result in one cycle. It includes a nested vectored interrupt controller (NVIC) block with 32 interrupt inputs and a Wakeup Interrupt Controller (WIC). The WIC can wake the processor up from the Deep Sleep mode, allowing power to be switched off to the main processor when the chip is in the Deep Sleep mode. The Cortex-M0 CPU provides a Non-Maskable Interrupt (NMI) input, which is made available to the user when it is not in use for system functions requested by the user.

The CPU also includes a debug interface, the serial wire debug (SWD) interface, which is a 2-wire form of JTAG; the debug configuration used for CCG1 has four break-point (address) comparators and two watchpoint (data) comparators.

#### Flash

The CCG1 device has a flash module with a flash accelerator, tightly coupled to the CPU to improve average access times from the flash block. The flash block is designed to deliver 1 wait-state (WS) access time at 48 MHz and 0-WS access time at 24 MHz. The flash accelerator delivers 85% of single-cycle SRAM access performance on average. Part of the flash module can be used to emulate EEPROM operation if required.

#### SROM

A supervisory ROM that contains boot and configuration routines is provided.

#### System Resources

#### Power System

The power system is described in detail in the section Power on page 6. It provides assurance that voltage levels are as required for each respective mode and either delay mode entry (on power-on reset (POR), for example) until voltage levels are as required for proper function or generate resets (Brown-Out Detect (BOD)) or interrupts (Low Voltage Detect (LVD)). The CCG1 operates with a single external supply over the range of 1.8 to 5.5 V and has three different power modes: Active, Sleep, and Deep Sleep; transitions between modes are managed by the power system.

#### Serial Communication Blocks (SCB)

The CCG1 has one SCB, which can implement an  $I^2C$  interface. The hardware  $I^2C$  block implements a full multi-master and slave interface (it is capable of multimaster arbitration). This block is capable of operating at speeds of up to 1 Mbps (Fast Mode Plus) and has flexible buffering options to reduce interrupt overhead and latency for the CPU. It also supports EZ- $I^2C$  that creates a mailbox address range in the memory of the CCG1 and effectively reduces  $I^2C$  communication to reading from and writing to an array in memory. In addition, the block supports an 8-deep FIFO for receive and transmit which, by increasing the time given for the CPU to read data, greatly reduces the need for clock stretching caused by the CPU not having read data on time.

The  $I^2C$  peripheral is compatible with the  $I^2C$  Standard-mode, Fast-mode, and Fast-mode Plus devices, as defined in the NXP  $I^2C$ -bus specification and user manual (UM10204). The  $I^2C$  bus I/O is implemented with GPIO in open-drain modes.

The CCG1 is not completely compliant with the I<sup>2</sup>C spec in the following respects:

- GPIO cells are not overvoltage tolerant and, therefore, cannot be hot-swapped or powered up independently of the rest of the I<sup>2</sup>C system.
- Fast-mode Plus has an I<sub>OL</sub> specification of 20 mA at a V<sub>OL</sub> of 0.4 V. The GPIO cells can sink a maximum of 8 mA I<sub>OL</sub> with a V<sub>OL</sub> maximum of 0.6 V.
- Fast-mode and Fast-mode Plus specify minimum Fall times, which are not met with the GPIO cell; Slow strong mode can help meet this spec depending on the Bus Load.
- When the SCB is an I<sup>2</sup>C Master, it interposes an IDLE state between NACK and Repeated Start; the I<sup>2</sup>C spec defines Bus free as following a Stop condition so other Active Masters do not intervene but a Master that has just become activated may start an Arbitration cycle.
- When the SCB is in the I<sup>2</sup>C Slave mode, and Address Match on External Clock is enabled (EC\_AM = 1) along with operation in the internally clocked mode (EC\_OP = 0), then its I<sup>2</sup>C address must be even.

### GPIO

The CCG1 has up to 11 GPIOs, which are configured for various functions. Refer to the pinout tables for the definitions. The GPIO block implements the following:

- Eight drive strength modes:
  - Analog input mode (input and output buffers disabled)
  - Input only
  - Weak pull-up with strong pull-down
  - □ Strong pull-up with weak pull-down
  - Open drain with strong pull-down
  - Open drain with strong pull-up
  - □ Strong pull-up with strong pull-down
  - Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTL).
- Individual control of input and output buffer enabling/disabling in addition to the drive strength modes.
- Hold mode for latching previous state (used for retaining I/O state in Deep Sleep mode).
- Selectable slew rates for dV/dt related noise control to improve EMI.

During power-on and reset, the I/O pins are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network, known as a high-speed I/O matrix, is used to multiplex between various signals that may connect to an I/O pin.



### **Pin Definitions**

Table 1 provides the pin definition for 35-ball WLCSP for the Active Cable application. Refer to Table 20 on page 13 for part numbers to package mapping.

Table 1.	Pin Definition	s for 35-ball WLCSP	for Active Cable Application
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Functional Pins	Ball Number	Туре	Description
CC1_RX	C4	I	CC1 control 0: TX enabled z: RX sense
CC1_TX	D7	0	Configuration Channel 1
SWD_IO	D1	I/O	SWD I/O
SWD_CLK	C1	Ι	SWD clock
I2C_SCL	B1	I/O	I <sup>2</sup> C clock signal
I2C_SDA	B2	I/O	I <sup>2</sup> C data signal
I2C_INT	A2	I/O	I <sup>2</sup> C_INT signal
XRES	B6		Reset
VCCD	A7	POWER	Connect a 1-µF capacitor between VCCD and ground.
VDDD	C7	POWER	VCONN supply
VDDA	C7	POWER	VCONN supply
VSSA	B7	GND	Analog ground
CC_VREF	C5	I	Data reference signal for CC lines
ADC_BYPASS	E7	I	Bypass capacitor for internal analog circuits
TX_U	B3	0	Signals for internal use only. The TX_U output signal should be connected
TX_M	B5	Ι	to the TX_M signal
TX_REF_IN	D3	Ι	Reference signal for internal use. Connect to TX_REF output via a 2.4K 1% resistor
TX_GND	A3	Ι	Connect to GND via 2K 1% resistor
TX_REF_OUT	D4	0	Reference signal generated by connecting internal current source to 0 and 2K external resistors
RA_DISCONNECT	E4	0	Optional control signal to remove RA after assertion of VCONN 0: RA disconnected 1: RA connected
VCONN_DET	C6	I	Local VCONN detection signal 0: VCONN is not locally applied (respond to SOP") 1: VCONN is locally applied (respond to SOP')
CC1_LPREF	A5	Ι	Reference signal for internal use. Connect to the output of resistor divider from VDDD.
RA_FAR_DISCONNECT	E5	0	Optional control signal to remove RA after assertion of VCONN (NC for 2 chip/cable) 0: RA disconnected 1: RA connected
BYPASS	D5	I	Bypass capacitor for internal analog circuits
CC1_LPRX	C3	I	Configuration channel 1 RX signal for Low Power States
GPIO_0	A1	I	Optional control signal to remove RA after assertion of VCONN Z: CCG1 responds to SOP' only 0: CCG1 responds to SOP' or SOP" based on VCONN presence
GPIO_1	A4	I/O	General-purpose I/O
GPIO_2	A6	I/O	General-purpose I/O
GPIO_3	B4	I/O	General-purpose I/O

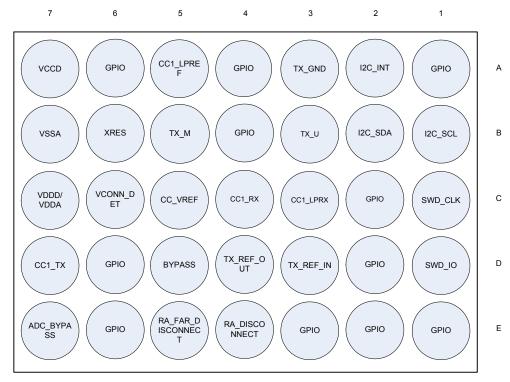




Functional Pins	Ball Number	Туре	Description
GPIO_4	C2	I/O	General-purpose I/O
GPIO_5	D2	I/O	General-purpose I/O
GPIO_6	D6	I/O	General-purpose I/O
GPIO_7	E1	I/O	General-purpose I/O
GPIO_8	E2	I/O	General-purpose I/O
GPIO_9	E3	I/O	General-purpose I/O
GPIO_10	E6	I/O	General-purpose I/O

#### Table 1. Pin Definitions for 35-ball WLCSP for Active Cable Application (continued)

### Pinouts



#### Figure 2. 35-Ball WLCSP Pinout



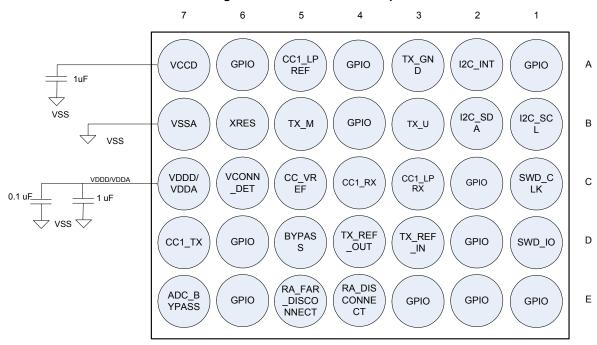
### Power

The following power system diagram shows the minimum set of power supply pins as implemented for the CCG1. The system has one regulator in Active mode for the digital circuitry. There is no analog regulator; the analog circuits run directly from the VDDA input. There is a separate regulator for the Deep Sleep mode. There is a separate low-noise regulator for the bandgap. The supply voltage range is 1.8 to 5.5 V with all functions and circuits operating over that range.

The CCG1 is powered by an external power supply that can be anywhere in the range of 1.8 to 5.5 V. This range is also designed for battery-powered operation. For example, the chip can be powered from a battery system that starts at 3.5 V and works down to 1.8 V. In this mode, the internal regulator of the CCG1 supplies the internal logic and the VCCD output of the CCG1 must be bypassed to ground via an external capacitor (in the range of 1 to 1.6  $\mu$ F; X5R ceramic or better). No voltage source should be applied to this pin.

VDDA and VDDD must be shorted together; the grounds, VSSA and VSS must also be shorted together. Bypass capacitors must be used from VDDD to ground. The typical practice for systems in this frequency range is to use a capacitor in the 1- $\mu$ F range in parallel with a smaller capacitor (0.1  $\mu$ F, for example). Note that these are simply rules of thumb and that, for critical applications, the PCB layout, lead inductance, and the bypass capacitor parasitic should be simulated to design and obtain optimal bypassing.

Example of bypass schemes follows.



#### Figure 3. 35-ball WLCSP Example



### **Electrical Specifications**

### **Absolute Maximum Ratings**

### Table 2. Absolute Maximum Ratings<sup>[8]</sup>

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/ Conditions
SID1	V <sub>DDD_ABS</sub>	Digital supply relative to V <sub>SSD</sub>	-0.50	-	6.00	V	Absolute max
SID2	V <sub>CCD_ABS</sub>	Direct digital core voltage input relative to $V_{\text{SSD}}$	-0.50	-	1.95	V	Absolute max
SID3	V <sub>GPIO_ABS</sub>	GPIO voltage	-0.50	-	V <sub>DDD</sub> +0.50	V	Absolute max
SID4	I <sub>GPIO_ABS</sub>	Maximum current per GPIO	-25.00	-	25.00	mA	Absolute max
SID5	I <sub>GPIO_injection</sub>	GPIO injection current, Max for V <sub>IH</sub> > V <sub>DDD</sub> , and Min for V <sub>IL</sub> < V <sub>SS</sub>	-0.50	_	0.50	mA	Absolute max, current injected per pin
BID44	ESD_HBM	Electrostatic discharge human body model	2200.00	_	-	V	-
BID45	ESD_CDM	Electrostatic discharge charged device model	500.00	_	_	V	-
BID46	LU	Pin current for latch-up	-200.00	_	200.00	mA	-

### **Device-Level Specifications**

All specifications are valid for –40 °C  $\leq$  T<sub>A</sub>  $\leq$  85 °C and T<sub>J</sub>  $\leq$  100 °C. Specifications are valid for 1.8 V to 5.5 V, except where noted.

### Table 3. DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID53	V <sub>DDD</sub>	Power supply input voltage	1.80	_	5.50	V	With regulator enabled
SID54	V <sub>CCD</sub>	Output voltage (for core logic)	-	1.80	-	V	-
SID55	C <sub>EFC</sub>	External regulator voltage bypass	1.00	1.30	1.60	μF	X5R ceramic or better
SID56	C <sub>EXC</sub>	Power supply decoupling capacitor	-	1.00	-	μF	X5R ceramic or better
Active Mo	de, V <sub>DDD</sub> = 1.8 to	5.5 V. Typical values measured at V	/ <sub>DD</sub> = 3.3 V				·
SID19	I <sub>DD14</sub>	Execute from flash; CPU at 48 MHz	-	12.80	-	mA	T = 25 °C
SID20	I <sub>DD15</sub>	Execute from flash; CPU at 48 MHz	-	-	13.80	mA	-
Sleep Mod	e, V <sub>DDD</sub> = 1.8 to	5.5 V					-
SID25A	I <sub>DD20A</sub>	I <sup>2</sup> C wakeup and comparators on	_	1.70	2.2 0	mA	-
Deep Slee	p Mode, V <sub>DDD</sub> =	1.8 to 3.6 V (Regulator on)					
SID31	I <sub>DD26</sub>	I <sup>2</sup> C wakeup on	_	1.30	_	μA	T = 25 °C, 3.6 V
SID32	I <sub>DD27</sub>	I <sup>2</sup> C wakeup on	-	-	50.00	μA	T = 85 °C
Deep Slee	p Mode, V <sub>DDD</sub> =	3.6 to 5.5 V				•	
SID34	I <sub>DD29</sub>	I <sup>2</sup> C wakeup	-	15.00	_	μA	T = 25 °C, 5.5 V
XRES Cur	rent					•	
SID307	I <sub>DD_XR</sub>	Supply current while XRES asserted	-	2.00	5.00	mA	-

Note

<sup>8.</sup> Usage above the absolute maximum conditions listed in Table 2 may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.



#### Table 4. AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/ Conditions
SID48	F <sub>CPU</sub>	CPU frequency	DC	-	48.00	MHz	$1.8 \leq V_{DD} \leq 5.5$
SID49	T <sub>SLEEP</sub>	Wakeup from sleep mode	_	0.00	_	μs	Guaranteed by characterization
SID50	T <sub>DEEPSLEEP</sub>	Wakeup from Deep Sleep mode	_	_	25.00	μs	24 MHz IMO. Guaranteed by characterization
SID52	T <sub>RESETWIDTH</sub>	External reset pulse width	1.00	-	_	μs	Guaranteed by characterization

I/O

### Table 5. I/O DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/ Conditions
SID57	V <sub>IH</sub> <sup>[9]</sup>	Input voltage high threshold	0.70 × V <sub>DDD</sub>	_	-	V	CMOS Input
SID58	V <sub>IL</sub>	Input voltage low threshold	-	-	0.30 × V <sub>DDD</sub>	V	CMOS Input
SID241	V <sub>IH</sub> <sup>[9]</sup>	LVTTL input, V <sub>DDD</sub> < 2.7 V	0.70 × V <sub>DDD</sub>	-	_	V	-
SID242	V <sub>IL</sub>	LVTTL input, V <sub>DDD</sub> < 2.7 V	_	-	0.30 × V <sub>DDD</sub>	V	_
SID243	V <sub>IH</sub> <sup>[9]</sup>	LVTTL input, $V_{DDD} \ge 2.7 \text{ V}$	2.00	-	-	V	-
SID244	V <sub>IL</sub>	LVTTL input, $V_{DDD} \ge 2.7 \text{ V}$	-	-	0.80	V	-
SID59	V <sub>OH</sub>	Output voltage high level	V <sub>DDD</sub> -0.60	-	-	V	$I_{OH}$ = 4 mA at 3 V V <sub>DDD</sub>
SID60	V <sub>OH</sub>	Output voltage high level	V <sub>DDD</sub> -0.50	-	_	V	I <sub>OH</sub> = 1 mA at 1.8 V V <sub>DDD</sub>
SID61	V <sub>OL</sub>	Output voltage low level	-	-	0.60	V	$I_{OL}$ = 4 mA at 1.8 V $V_{DDD}$
SID62	V <sub>OL</sub>	Output voltage low level	-	-	0.60	V	$I_{OL}$ = 8 mA at 3 V $V_{DDD}$
SID62A	V <sub>OL</sub>	Output voltage low level	-	-	0.40	V	$I_{OL}$ = 3 mA at 3 V $V_{DDD}$
SID63	R <sub>PULLUP</sub>	Pull-up resistor	3.50	5.60	8.50	kΩ	-
SID64	R <sub>PULLDOWN</sub>	Pull-down resistor	3.50	5.60	8.50	kΩ	-
SID65	IL	Input leakage current (absolute value)	-	-	2.00	nA	25 °C, V <sub>DDD</sub> = 3.0 V
SID65A	I <sub>IL_CTBM</sub>	Input leakage current (absolute value) for analog pins	-	-	4.00	nA	-
SID66	C <sub>IN</sub>	Input capacitance	-	-	7.00	pF	-
SID67	V <sub>HYSTTL</sub>	Input hysteresis LVTTL	15.00	40.00	_	mV	$V_{DDD} \ge 2.7 \text{ V.}$ Guaranteed by characterization
SID68	V <sub>HYSCMOS</sub>	Input hysteresis CMOS	200.00	_	_	mV	$V_{DDD} \ge 4.5 \text{ V.}$ Guaranteed by characterization
SID69	I <sub>DIODE</sub>	Current through protection diode to $V_{DD}/V_{SS}$	_	-	100.00	μA	Guaranteed by characterization



### Table 5. I/O DC Specifications (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID69A	I <sub>TOT_GPIO</sub>	Maximum Total Source or Sink Chip Current	1	1	200.00	mA	Guaranteed by characterization

### Table 6. I/O AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/ Conditions
SID70	T <sub>RISEF</sub>	Rise time	2.00	_	12.00	ns	3.3 V V <sub>DDD</sub> , Cload = 25 pF
SID71	T <sub>FALLF</sub>	Fall time	2.00	-	12.00	ns	3.3 V V <sub>DDD</sub> , Cload = 25 pF

XRES

### Table 7. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/ Conditions
SID77	V <sub>IH</sub>	Input voltage high threshold	0.70 × V <sub>DDD</sub>	-	-	V	CMOS input
SID78	V <sub>IL</sub>	Input voltage low threshold	_	-	0.30 × V <sub>DDD</sub>	V	CMOS input
SID79	R <sub>PULLUP</sub>	Pull-up resistor	3.50	5.60	8.50	kΩ	-
SID80	C <sub>IN</sub>	Input capacitance	-	3.00	_	pF	-
SID81	V <sub>HYSXRES</sub>	Input voltage hysteresis	_	100.00	_	mV	Guaranteed by characterization
SID82	I <sub>DIODE</sub>	Current through protection diode to $V_{DDD}/V_{SS}$	-	-	100.00	μA	Guaranteed by characterization

### **Digital Peripherals**

The following specifications apply to the Timer/Counter/PWM peripherals in the Timer mode.

Pulse Width Modulation (PWM) for VSEL and CUR\_LIM Pins

### Table 8. PWM AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID140	T <sub>PWMFREQ</sub>	Operating frequency	-	-	48.00	MHz	-
SID141	T <sub>PWMPWINT</sub>	Pulse width (internal)	42.00	-	-	ns	-
SID142	T <sub>PWMEXT</sub>	Pulse width (external)	42.00	-	-	ns	-
SID143	T <sub>PWMKILLINT</sub>	Kill pulse width (internal)	42.00	-	-	ns	-
SID144	T <sub>PWMKILLEXT</sub>	Kill pulse width (external)	42.00	-	-	ns	-
SID145	T <sub>PWMEINT</sub>	Enable pulse width (internal)	42.00	-	-	ns	-
SID146	T <sub>PWMENEXT</sub>	Enable pulse width (external)	42.00	-	-	ns	-
SID147	T <sub>PWMRESWINT</sub>	Reset pulse width (internal)	42.00	-	-	ns	-
SID148	T <sub>PWMRESWEXT</sub>	Reset pulse width (external)	42.00	-	-	ns	_



### l<sup>2</sup>C

### Table 9. Fixed I<sup>2</sup>C DC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID149	I <sub>I2C1</sub>	Block current consumption at 100 kHz	-	_	10.50	μA	-
SID150	I <sub>I2C2</sub>	Block current consumption at 400 kHz	-	_	135.00	μA	-
SID151	I <sub>I2C3</sub>	Block current consumption at 1 Mbps	_	_	310.00	μA	-
SID152	I <sub>I2C4</sub>	I <sup>2</sup> C enabled in Deep Sleep mode	-	-	1.40	μA	_

### Table 10. Fixed I<sup>2</sup>C AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Мах	Units	<b>Details/Conditions</b>
SID153	F <sub>I2C1</sub>	Bit rate	-	-	1.00	Mbps	_

#### Memory

#### Table 11. Flash DC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID173	V <sub>PE</sub>	Erase and program voltage	1.80	-	5.50	V	_

#### Table 12. Flash AC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID174	T <sub>ROWWRITE</sub> <sup>[10]</sup>	Row (block) write time (erase and program)	-	_	20.00	ms	Row (block) = 128 bytes
SID175	T <sub>ROWERASE</sub> <sup>[10]</sup>	Row erase time	-	-	13.00	ms	_
SID176	T <sub>ROWPROGRAM</sub> <sup>[10]</sup>	Row program time after erase	-	-	7.00	ms	_
SID178	T <sub>BULKERASE</sub> <sup>[10]</sup>	Bulk erase time (32 KB)	-	-	35.00	ms	_
SID180	T <sub>DEVPROG</sub> <sup>[10]</sup>	Total device program time	-	-	7.00	seconds	Guaranteed by characterization
SID181	F <sub>END</sub>	Flash endurance	100 K	-	-	cycles	Guaranteed by characterization
SID182	F <sub>RET</sub> <sup>[11]</sup>	Flash retention. $T_A \le 55$ °C, 100 K P/E cycles	20	-	-	years	Guaranteed by characterization
SID182A	-	Flash retention. $T_A \le 85 \text{ °C}$ , 10 K P/E cycles	10	_	_	years	Guaranteed by characterization
SID182B	-	Flash retention. 85 °C < T <sub>A</sub> ≤ 105 °C, 10K P/E cycles	3	_	-	years	Guaranteed by characterization

### System Resources

Power-on-Reset (POR) with Brown Out

#### Table 13. Imprecise Power On Reset (PRES)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID185	V <sub>RISEIPOR</sub>	Rising trip voltage	0.80	-	1.45	V	Guaranteed by characterization
SID186	V <sub>FALLIPOR</sub>	Falling trip voltage	0.75	-	1.40	V	Guaranteed by characterization
SID187	V <sub>IPORHYST</sub>	Hysteresis	15.0	-	200.0	mV	Guaranteed by characterization

Note

10. It can take as much as 20 milliseconds to write to flash. During this time the device should not be Reset, or flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.

11. Cypress provides a retention calculator to calculate the retention lifetime based on customers' individual temperature profiles for operation over the -40 °C to +105 °C ambient temperature range. Contact customercare@cypress.com.



#### Table 14. Precise Power On Reset (POR)

Spec ID	Parameter	Description	Min	Тур	Мах	Units	Details/Conditions
SID190		BOD trip voltage in active and sleep modes	1.64	-	-	V	Guaranteed by characterization
SID192	V <sub>FALLDPSLP</sub>	BOD trip voltage in Deep Sleep	1.40	-	-	V	Guaranteed by characterization

#### SWD Interface

#### Table 15. SWD Interface Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID213	F_SWDCLK1	$3.3 \text{ V} \leq \text{V}_{\text{DDD}} \leq 5.5 \text{ V}$	-	-	14.00	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID214	F_SWDCLK2	$1.8 \text{ V} \le \text{V}_{\text{DDD}} \le 3.3 \text{ V}$	_	_	7.00	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID215	T_SWDI_SETUP	T = 1/f SWDCLK	0.25*T	-	-	ns	Guaranteed by characterization
SID216	T_SWDI_HOLD	T = 1/f SWDCLK	0.25*T	-	-	ns	Guaranteed by characterization
SID217	T_SWDO_VALID	T = 1/f SWDCLK	-	-	0.50*T	ns	Guaranteed by characterization
SID217A	T_SWDO_HOLD	T = 1/f SWDCLK	1	_	-	ns	Guaranteed by characterization

#### Internal Main Oscillator

### Table 16. IMO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID218	I <sub>IMO1</sub>	IMO operating current at 48 MHz	_	Ι	1000.00	μA	_

#### Table 17. IMO AC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID223	F <sub>IMOTOL1</sub>	Frequency variation	-	-	±2.00	%	With API-called calibration
SID226	T <sub>STARTIMO</sub>	IMO startup time	-	-	12.00	μs	-
SID229	T <sub>JITRMSIMO3</sub>	RMS Jitter at 48 MHz	-	139.00	_	ps	_

Internal Low-Speed Oscillator

### Table 18. ILO DC Specifications

(Guaranteed by Design)

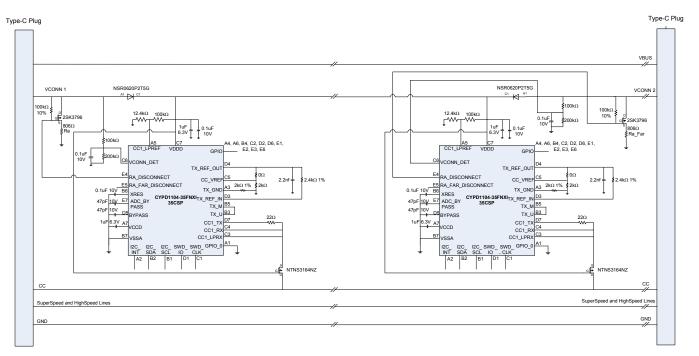
Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID231	I <sub>ILO1</sub>	ILO operating current at 32 kHz	-	0.30	1.05	μA	Guaranteed by characterization
SID233	I <sub>ILOLEAK</sub>	ILO leakage current	_	2.00	15.00	nA	Guaranteed by design

### Table 19. ILO AC Specifications

Spec ID	Parameter	Description	Min	Тур	Мах	Units	Details/Conditions
SID234	T <sub>STARTILO1</sub>	ILO startup time	_	_	2.00	ms	Guaranteed by characterization
SID236	T <sub>ILODUTY</sub>	ILO duty cycle	40.00	50.00	60.00	%	Guaranteed by characterization
SID237	F <sub>ILOTRIM1</sub>	32-kHz trimmed frequency	15.00	32.00	50.00	kHz	±60% with trim



## **Applications in Detail**



#### Figure 4. Two Chip/Active Cable Application Example



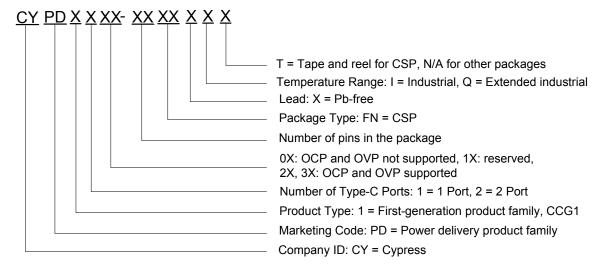
### **Ordering Information**

The part number and features are listed in Table 20.

### Table 20. CCG1 Ordering Information

Part Number <sup>[12]</sup>	Application	Type-C Ports <sup>[13]</sup>	Overcurrent Protection	Overvoltage Protection	Termination Resistor <sup>[14]</sup>	Role <sup>[15]</sup>	Package	Si ID
CYPD1104-35FNXIT	Active Cable, EMCA	1	No	No	$R_{a}^{[16]}$	Active Cable	35-WLCSP <sup>[17]</sup>	0493

### **Ordering Code Definitions**



Notes 12. All part numbers support: Input voltage range from 1.8 to 5.5 V. Industrial parts support -40 °C to +85 °C, Extended Industrial parts support -40 °C to 105 °C. 13. Number of USB Type-C Ports Supported . 14. Default V<sub>CONN</sub> Termination. 15. PD Pole

15. PD Role.
 16. Type-C Cable Termination.
 17. 35-WLCSP pinout.



### Packaging

### Table 21. Package Characteristics

Parameter	Description	Conditions	Min	Тур	Max	Units
T <sub>A</sub> (35-CSP)	Operating ambient temperature	-	-40	25.00	85.00	°C
T <sub>J</sub> (35-CSP)	Operating junction temperature	-	-40	-	100.00	°C
T <sub>JA</sub>	Package θJA (35-CSP)	-	_	28.00	-	°C/Watt
T <sub>JC</sub>	Package θJC (35-CSP)	-	-	00.40	-	°C/Watt

#### Table 22. Solder Reflow Peak Temperature

Package	Maximum Peak Temperature	Maximum Time at Peak Temperature
35-ball WLCSP	260 °C	30 seconds

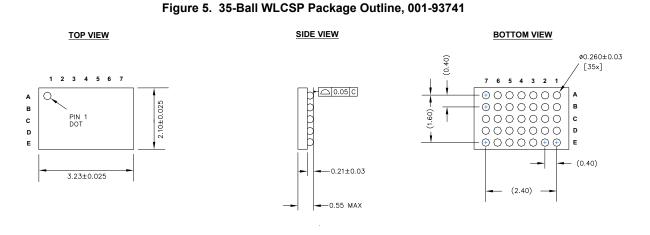
### Table 23. Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-2

Package	MSL
35-ball WLCSP	MSL 1

The center pad on the QFN package should be connected to ground (VSS) for best mechanical, thermal, and electrical performance. If not connected to ground, it should be electrically floating and not connected to any other signal.



### Package Diagram



NOTES:

1. REFERENCE JEDEC PUBLICATION 95, DESIGN GUIDE 4.18

2. ALL DIMENSIONS ARE IN MILLIMETERS

001-93741 \*\*



## Acronyms

### Table 24. Acronyms Used in this Document

Acronym	Description
ADC	analog-to-digital converter
API	application programming interface
ARM®	advanced RISC machine, a CPU architecture
CC	Configuration Channel
CPU	central processing unit
CRC	cyclic redundancy check, an error-checking protocol
CS	Current Sense
DFP	downstream facing port
DIO	digital input/output, GPIO with only digital capabilities, no analog. See GPIO.
EEPROM	electrically erasable programmable read-only memory
EMI	electromagnetic interference
ESD	electrostatic discharge
FPB	flash patch and breakpoint
FS	full-speed
GPIO	general-purpose input/output, applies to a PSoC pin
IC	integrated circuit
IDE	integrated development environment
I <sup>2</sup> C, or IIC	Inter-Integrated Circuit, a communications protocol
ILO	internal low-speed oscillator, see also IMO
IMO	internal main oscillator, see also ILO
I/O	input/output, see also GPIO, DIO, SIO, USBIO
LVD	low-voltage detect
LVTTL	low-voltage transistor-transistor logic
MCU	microcontroller unit
NC	no connect
NMI	nonmaskable interrupt
NVIC	nested vectored interrupt controller

#### Table 24. Acronyms Used in this Document (continued)

Acronym	Description
opamp	operational amplifier
OCP	Overcurrent protection
OVP	Overvoltage protection
РСВ	printed circuit board
PGA	programmable gain amplifier
PHY	physical layer
POR	power-on reset
PRES	precise power-on reset
PSoC <sup>®</sup>	Programmable System-on-Chip™
PWM	pulse-width modulator
RAM	random-access memory
RISC	reduced-instruction-set computing
RMS	root-mean-square
RTC	real-time clock
RX	receive
SAR	successive approximation register
SCL	I <sup>2</sup> C serial clock
SDA	I <sup>2</sup> C serial data
S/H	sample and hold
SPI	Serial Peripheral Interface, a communications protocol
SRAM	static random access memory
SWD	serial wire debug, a test protocol
ТХ	transmit
UART	Universal Asynchronous Transmitter Receiver, a communications protocol
UFP	upstream facing port
USB	Universal Serial Bus
USBIO	USB input/output, PSoC pins used to connect to a USB port
XRES	external reset I/O pin



### **Document Conventions**

### Units of Measure

### Table 25. Units of Measure

Symbol	Unit of Measure
°C	degrees Celsius
Hz	hertz
KB	1024 bytes
kHz	kilohertz
kΩ	kilo ohm
Mbps	megabits per second
MHz	megahertz
MΩ	mega-ohm
Msps	megasamples per second
μA	microampere
μF	microfarad
μs	microsecond
μV	microvolt
μW	microwatt
mA	milliampere
ms	millisecond
mV	millivolt
nA	nanoampere
ns	nanosecond
Ω	ohm
pF	picofarad
ppm	parts per million
ps	picosecond
S	second
sps	samples per second
V	volt



# **Revision History**

Description Title: CYPD1104-35FNXIT Datasheet USB Type-C Port Controller with Power Delivery Document Number: 001-97904				
Revision	ECN	Orig. of Change	Submission Date	Description of Change
**	4788646	VGT	06/09/2015	New datasheet



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Revised June 9, 2015

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